

# RT3WLMM

Composite Transistor  
For Low Frequency Amplify Application  
Silicon Epitaxial Type

## DESCRIPTION

RT3WLMM is a composite transistor built with 2SC3052 chip and 2SA1235A chip in SC-88 package.

## FEATURE

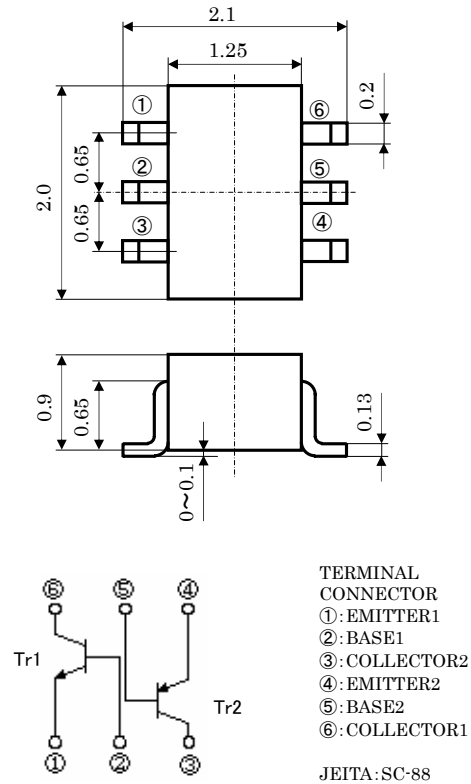
- Silicon epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

## APPLICATION

For low frequency amplify application

## OUTLINE DRAWING

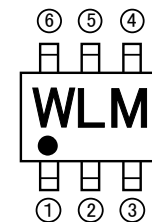
Unit: mm



## MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING		UNIT
		Tr1	Tr2	
V <sub>CBO</sub>	Collector to Base voltage	50	60	V
V <sub>EBO</sub>	Emitter to Base voltage	6		V
V <sub>CEO</sub>	Collector to Emitter voltage	50		V
I <sub>C</sub>	Collector current	200		mA
P <sub>C(Total)</sub>	Collector dissipation (Ta=25°C)	150		mW
T <sub>j</sub>	Junction temperature	+125		°C
T <sub>stg</sub>	Storage temperature	-55~+125		°C

## MARKING



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## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V(BR)CEO	Collector to Emitter break down voltage	$I_C=100\mu A, R_{BE}=\infty$	50	-	-	V
ICBO	Collector cut off current	$V_{CB}=50V, I_E=0$	-	-	0.1	$\mu A$
IEBO	Emitter cut off current	$V_{EB}=6V, I_C=0$	-	-	0.1	$\mu A$
hFE*	DC forward current gain	$V_{CE}=6V, I_C=1mA$	150	-	500	-
hFE	DC forward current gain	$V_{CE}=6V, I_C=0.1mA$	90	-	-	-
VCE(sat)	Collector to Emitter saturation voltage	$I_C=100mA, I_B=10mA$	-	-	0.3	V
fT	Gain band width product	$V_{CE}=6V, I_E=-10mA$	-	200	-	MHZ
Cob	Collector output capacitance	(Tr1) $V_{CB}=6V, I_E=0, f=1MHz$	-	2.5	-	pF
		(Tr2) $V_{CB}=-6V, I_E=0, f=1MHz$	-	4.0	-	
NF	Noise figure	(Tr1) $V_{CE}=6V, I_E=0.1mA, f=1kHz, R_G=2k\Omega$	-	-	15	dB
		(Tr2) $V_{CE}=-6V, I_E=0.3mA, f=100Hz, R_G=10k\Omega$	-	-	20	

\* : It shows hFE classification in right table.

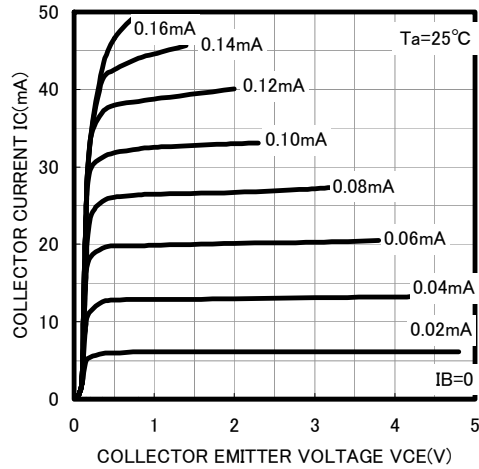
Item	E	F
hFE	150~300	250~500

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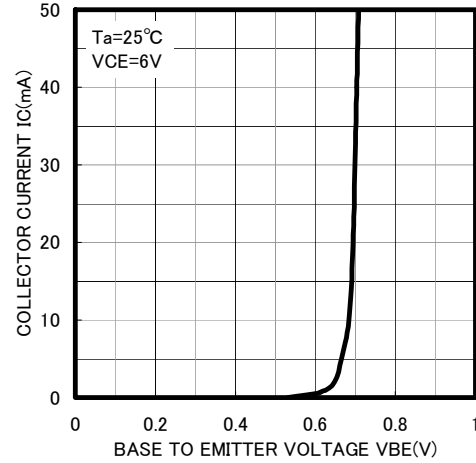
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## TYPICAL CHARACTERISTICS (Tr1)

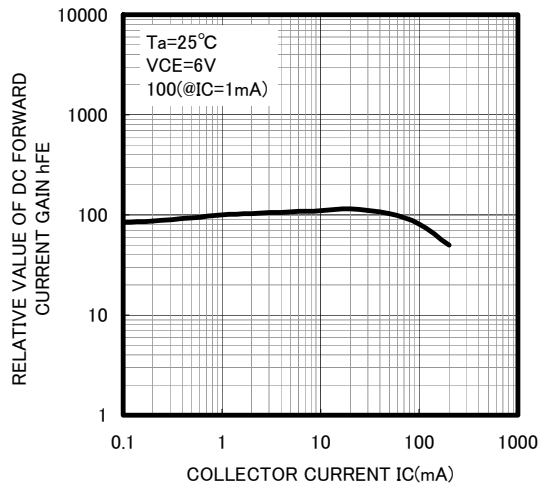
### COMMON EMITTER OUTPUT



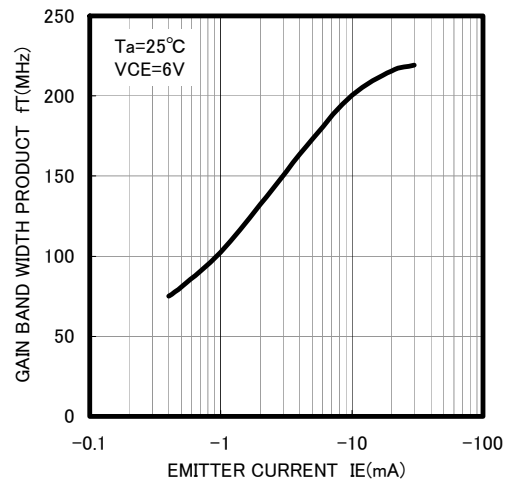
### COMMON EMITTER TRANSFER



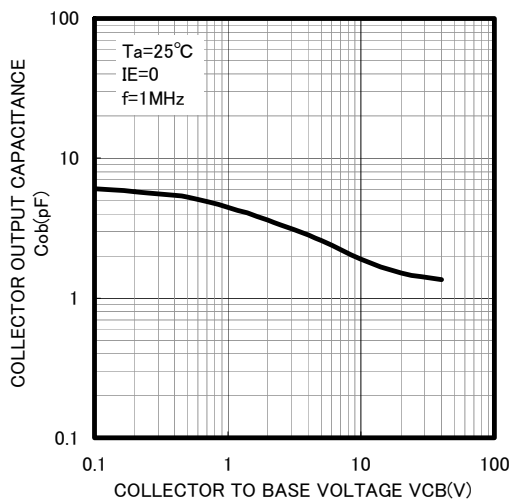
### DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



### GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



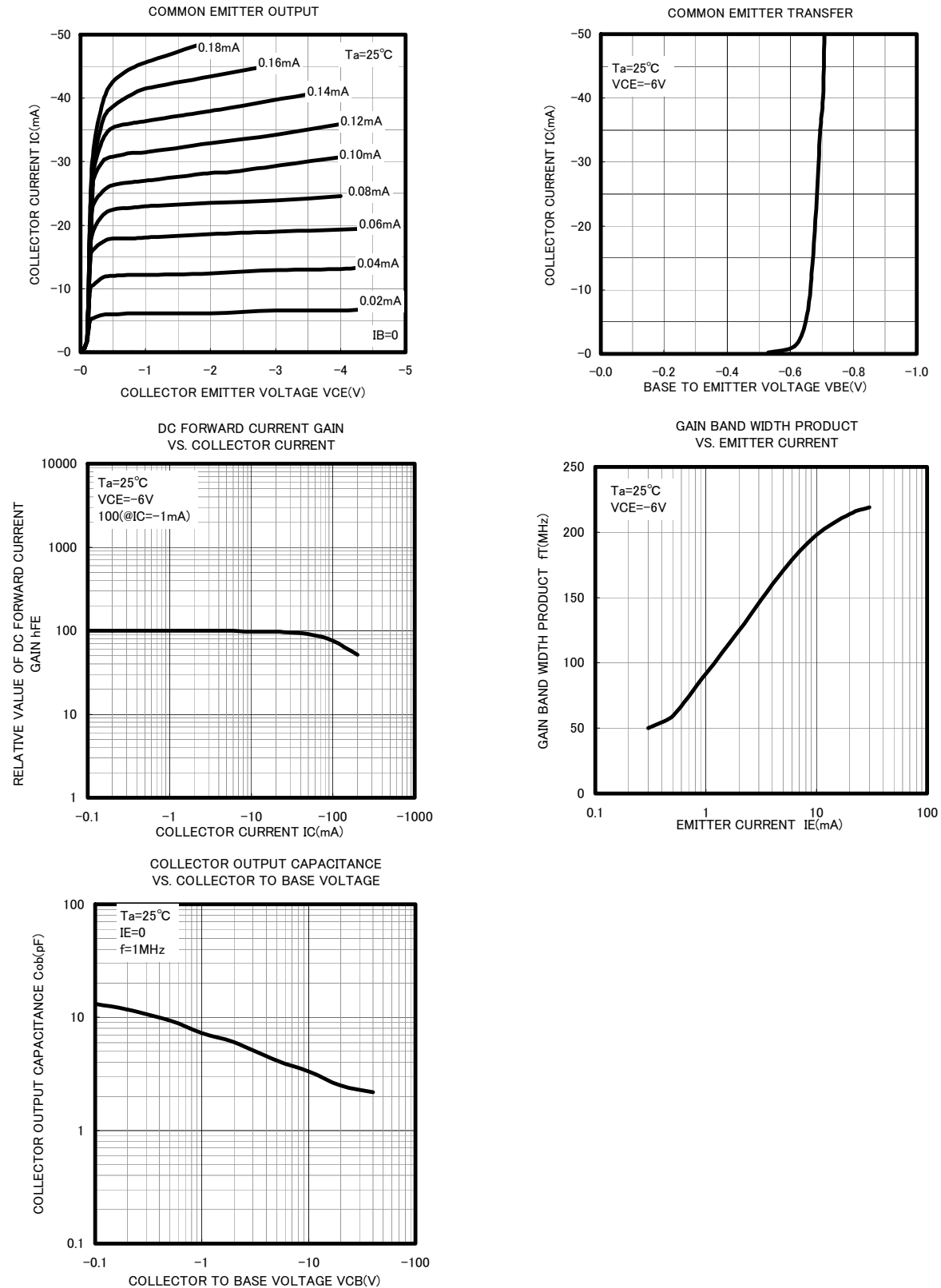
### COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



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## TYPICAL CHARACTERISTICS (Tr2)





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